

P0403BVG-VB Datasheet N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a	Q _g (Typ.)		
30	0.004 at V _{GS} = 10 V	18	6.8 nC		
	0.005 at V _{GS} = 4.5 V	16	0.0110		

SO-8

Top View

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FEATURES

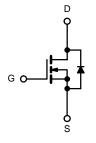
- · Halogen-free
- Trench Power MOSFET



- 100 % R_g Tested
- 100 % UIS Tested

APPLICATIONS

- Notebook CPU Core
 - High-Side Switch



N-Channel MOSFET

- 55 to 150

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	30	V	
Gate-Source Voltage	V_{GS}	± 20		
	T _C = 25 °C		18	
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	1-	16	
Continuous Diain Current (1) = 130 °C)	T _A = 25 °C	I _D	15 ^{b, c}	
	T _A = 70 °C		13 ^{b, c}	_
Pulsed Drain Current	I _{DM}	50	Α	
Ocationary Command Brain Binds Command	T _C = 25 °C	1-	3.8	
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	2.1 ^{b, c}	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	22	
Avalanche Energy	L=0.11111	E _{AS}	24	mJ
	T _C = 25 °C		4.5	
Maximum Dawar Dissination	T _C = 70 °C	D	2.8	14/
Maximum Power Dissipation	T _A = 25 °C	P _D	2.5 ^{b, c}	W
	T _A = 70 °C		1.6 ^{b, c}	1

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	38	50	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	22	28	7		

T_J, T_{stg}

Notes:

- a. Base on $T_C = 25$ °C.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under Steady State conditions is 85 °C/W.

Operating Junction and Storage Temperature Range

服务热线:400-655-8788

°C



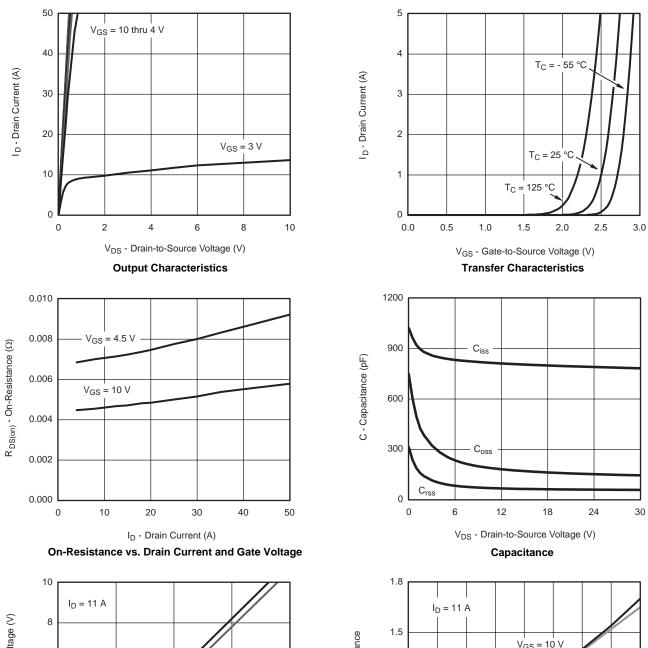
SPECIFICATIONS $T_J = 25 ^{\circ}\text{C}$ Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static	- ,			.,,,,		J	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$			28		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	I _D = 250 μA		- 6			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1.0		3.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 30 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			10	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
		V _{GS} = 10 V, I _D = 11 A		0.004		Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 10 A		0.005			
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 11 A		52		S	
Dynamic ^b	1 1			L			
Input Capacitance	C _{iss}			820			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		195		pF	
Reverse Transfer Capacitance	C _{rss}	50		73			
		V _{DS} = 15 V, V _{GS} = 10 V, I _D = 11 A		15	23	nC	
Total Gate Charge	Q _g	20 00 2		6.8	10.2		
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 11 \text{ A}$		2.5			
Gate-Drain Charge	Q _{gd}			2.3			
Gate Resistance	R_g	f = 1 MHz	0.36	1.8	3.6	Ω	
Turn-On Delay Time	t _{d(on)}			16	24		
Rise Time	t _r	V_{DD} = 15 V, R_L = 1.4 Ω		12	18		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 9 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		16	24		
Fall Time	t _f			10	20		
Turn-On Delay Time	t _{d(on)}			8	16	ns	
Rise Time	t _r	V_{DD} = 15 V, R_L = 1.4 Ω		10	20	- - -	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 9 \text{ A}, \ V_{GEN} = 10 \text{ V}, \ R_g = 1 \ \Omega$		16	24		
Fall Time	t _f			8	15		
Drain-Source Body Diode Characterist	ics			<u>'</u>	1		
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			25	^	
Pulse Diode Forward Current ^a	I _{SM}				50	A	
Body Diode Voltage	V_{SD}	I _S = 9 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			15	30	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			6	12	nC	
Reverse Recovery Fall Time				8			
Reverse Recovery Rise Time	t _b			7		ns	

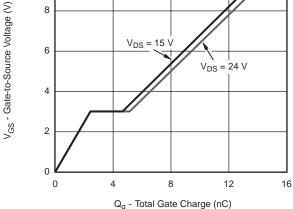
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

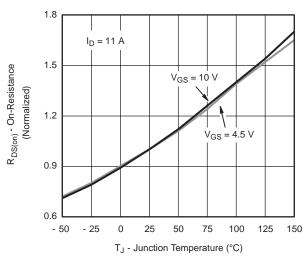
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





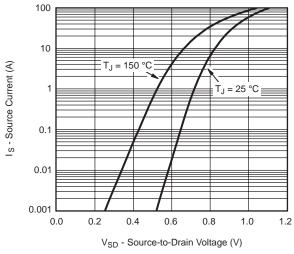


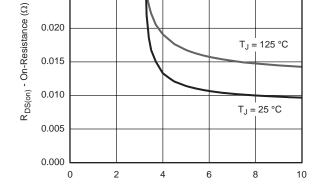
Gate Charge



On-Resistance vs. Junction Temperature





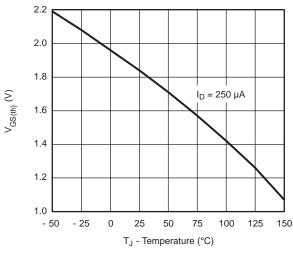


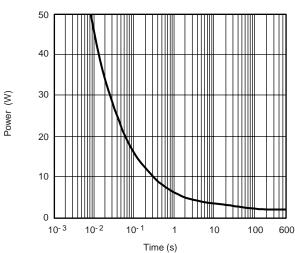
0.030

0.025

Source-Drain Diode Forward Voltage

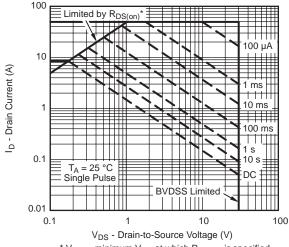






Threshold Voltage

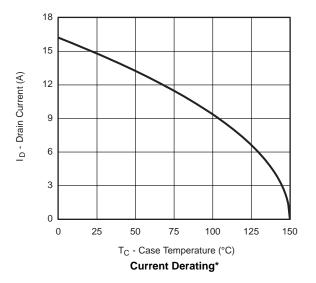
Single Pulse Power, Junction-to-Ambient

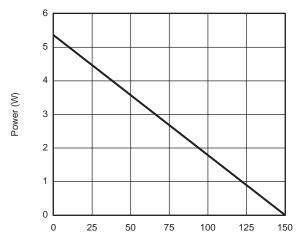


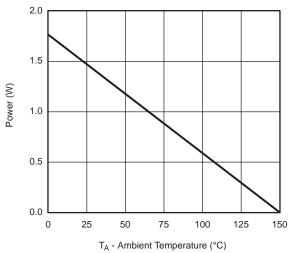
* $V_{GS} > \mbox{minimum } V_{GS}$ at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient







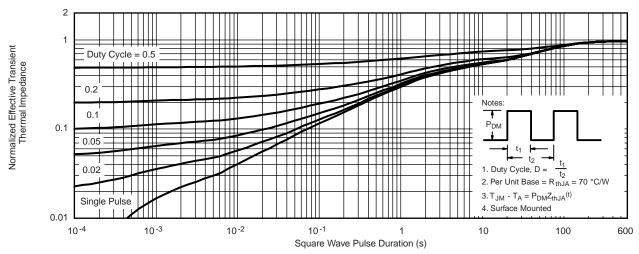


 $\ensuremath{\mathsf{T}}_C$ - Case Temperature (°C) $\ensuremath{\textbf{Power Derating, Junction-to-Foot}}$

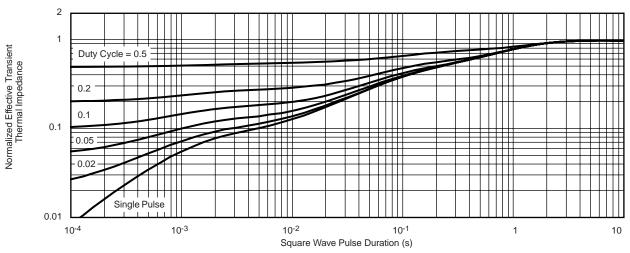
Power Derating, Junction-to-Ambient

^{*} The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



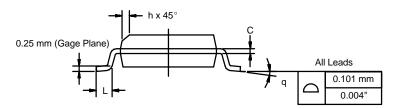
Normalized Thermal Transient Impedance, Junction-to-Foot



SOIC (NARROW): 8-LEADJEDEC Part Number: MS-012







	MILLIMETERS		INC	HES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
FCN: C-06527-Rev 11-Sen-06					

ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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